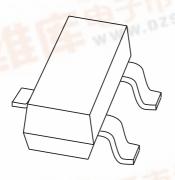
#### DISCRETE SEMICONDUCTORS

# DATA SHEET



## MMBT3904 NPN switching transistor

Product specification
Supersedes data of 2002 May 13

2002 Oct 04







### **NPN** switching transistor

#### **MMBT3904**

#### **FEATURES**

- Collector current capability I<sub>C</sub> = 200 mA
- Collector-emitter voltage  $V_{CEO} = 40 \text{ V}$ .

#### **APPLICATIONS**

• General switching and amplification.

#### **DESCRIPTION**

NPN switching transistor in a SOT23 plastic package. PNP complement: MMBT3906.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)
MMBT3904	7A*

#### Note

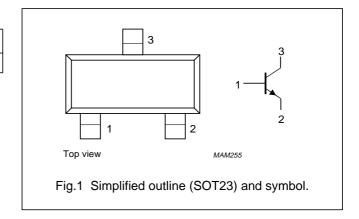
- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	40	V
I <sub>C</sub>	collector current (DC)	200	mA

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	V
I <sub>C</sub>	collector current (DC)		_	200	mA
I <sub>CM</sub>	peak collector current		_	200	mA
I <sub>BM</sub>	peak base current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

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## NPN switching transistor

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	RAMETER CONDITIONS			UNIT			
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	_	50	nA			
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 6 V	_	50	nA			
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; see Fig.2; note 1						
		I <sub>C</sub> = 0.1 mA	60	_				
		I <sub>C</sub> = 1 mA	80	_				
		I <sub>C</sub> = 10 mA	100	300				
		I <sub>C</sub> = 50 mA	60	_				
		I <sub>C</sub> = 100 mA	30	_				
V <sub>CEsat</sub>	collector-emitter saturation	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	_	200	mV			
	voltage	I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA	_	300	mV			
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	650	850	mV			
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA	_	950	mV			
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 5$ V; $f = 1$ MHz	_	4	pF			
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{BE} = 500 \text{ mV}$ ; $f = 1 \text{ MHz}$	_	8	pF			
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 20 V; f = 100 MHz	300	_	MHz			
F	noise figure	$I_C$ = 100 μA; $V_{CE}$ = 5 V; $R_S$ = 1 kΩ; $f$ = 10 Hz to 15.7 kHz	_	5	dB			
Switching ti	Switching times (between 10% and 90% levels); see Fig.3							
t <sub>d</sub>	delay time	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 1 mA;	_	35	ns			
t <sub>r</sub>	rise time	I <sub>Boff</sub> = −1 mA	_	35	ns			
t <sub>s</sub>	storage time		_	200	ns			
t <sub>f</sub>	fall time		_	50	ns			

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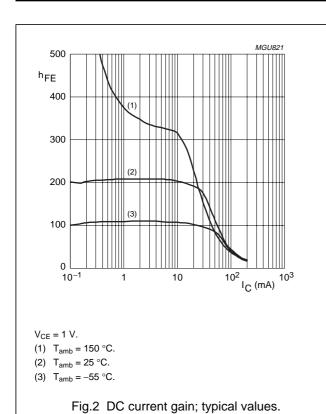
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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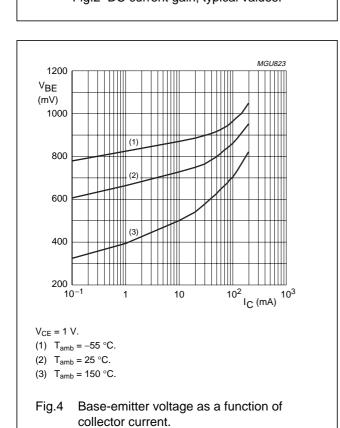
### NPN switching transistor

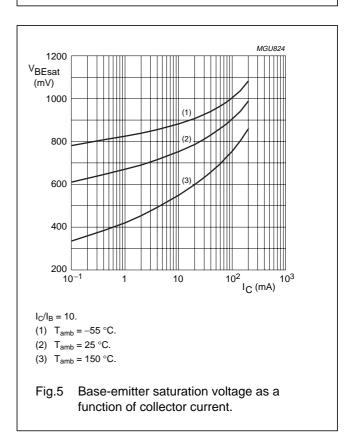
#### MMBT3904



MGI 1822 250  $I_{C}$ (mA) 150 100 (10) 50 0 8 VCE (V)  $T_{amb} = 25 \, ^{\circ}C.$ (1)  $I_B = 5.5 \text{ mA}.$ (5)  $I_B = 3 \text{ mA}.$ (9)  $I_B = 1 \text{ mA}.$ (6)  $I_B = 2.5 \text{ mA}.$ (10)  $I_B = 0.5 \text{ mA}$ . (2)  $I_B = 5 \text{ mA}$ . (3)  $I_B = 4.5 \text{ mA}.$ (7)  $I_B = 2 \text{ mA}$ . (4)  $I_B = 3.5 \text{ mA}.$ (8)  $I_B = 1.5 \text{ mA}.$ Collector current as a function of

collector-emitter voltage.





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## NPN switching transistor

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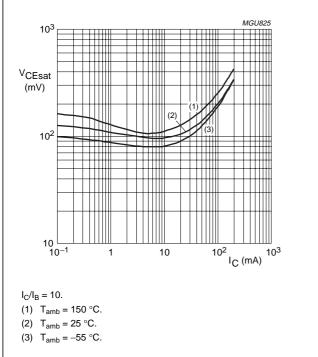
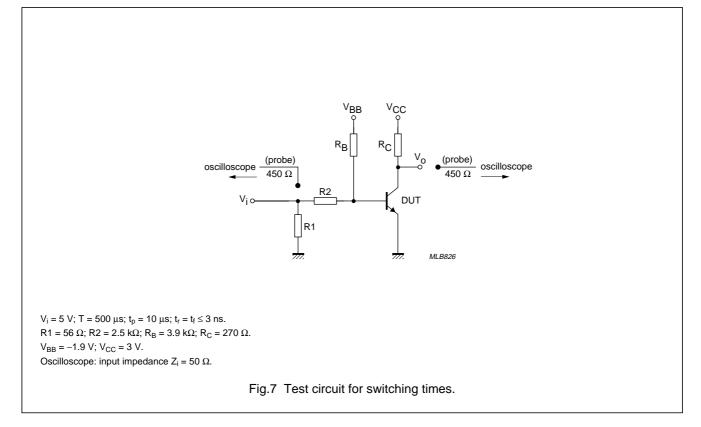


Fig.6 Collector-emitter saturation voltage as a function of collector current.



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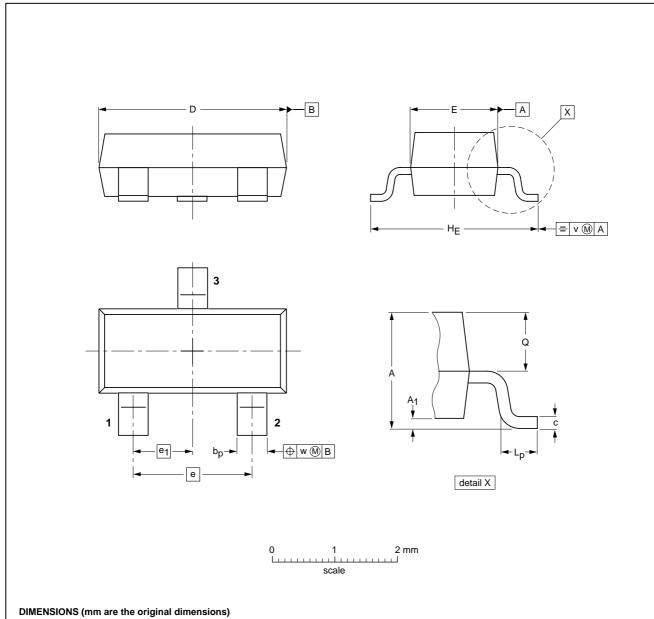
## NPN switching transistor

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



UNIT	Α	A <sub>1</sub> max.	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE	E REFER		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-97-02-28</del> 99-09-13

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#### NPN switching transistor

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LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
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#### **Contact information**

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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